

12500 TI Boulevard, MS 8640, Dallas, Texas 75243

PCN# 20140715000 Qualification of Fluorine Free ILD on CMOS9T Technology Change Notification / Sample Request

Date: 7/15/2014

To: Newark/Farnell PCN

Dear Customer:

This is an announcement of a change to a device that is currently offered by Texas Instruments. The details of this change are on the following pages.

We request you acknowledge receipt of this notification within **30** days of the date of this notice. Lack of acknowledgement of this notice within 30 days constitutes acceptance of the change. If you require samples or additional data to support your evaluation, please request within 30 days.

The changes discussed within this PCN will not take effect any earlier than **90** days from the date of this notification, unless customer agreement has been reached on an earlier implementation of the change. This notification period is per TI's standard process.

This notice does not change the end-of-life status of any product. Should product affected be on a previously issued product withdrawal/discontinuance notice, this notification does not extend the life of that product or change the life time buy offering/discontinuance plan.

For questions regarding this notice, contact your local Field Sales Representative or the PCN Manager (PCN www admin team@list.ti.com).

Sincerely,

PCN Team SC Business Services Phone: +1(214) 480-6037 Fax: +1(214) 480-6659

20140715000 Attachment: 1

Products Affected:

The devices listed on this page are a subset of the complete list of affected devices. According to our records, these are the devices that you have purchased within the past twenty-four (24) months. The corresponding customer part number is also listed, if available.

DEVICEADS1293CISQE/NOPB
LDC1000NHRT

CUSTOMER PART NUMBER

null null

Technical details of this Product Change follow on the next page(s).

PCN Num	ber:	20140715000 PCN Date: 07/15/20						/2014						
Title: Qualification of Fluorine Free ILD on CMOS9T 5V technology.														
Custome	r Contact:	PCN A	CN Manager Phone: +1(214)480-603						De	Dept: Quality Services				
*Propose	ate:	10/	15/20	014	Estimated Sample			Date Provided at						
		Т	Availability: Sample request											
Change T	ype: nbly Site			Assembly Process					Assembly Materials					
Desig						Specificat	ion	┢	Mechanical Specifica					
Test 9			П	Packing/Shipping/Labeling					Test Process					
Wafer	Bump Site			Wafer Bump Material					Wafer Bump Process					
Wafer	Fab Site			Wafer Fab Materials				\boxtimes	Wafer Fab Process					
				Part		er chang								
					PCI	N Detai	ls							
Descripti	on of Chang	e:												
This change notification is to announce the qualification of Fluorine Free ILD dielectric composition on the CMOS9T 5V technology. Current														
Chip Site Fab Process				Wafer Diameter			Fluorine ILD Composition							
MAINEFAB CMOS9T 5V			200mm			HDP = 4.5%, FSG=6.0%								
New														
Chip Site	ocess			Wafer Diameter		Fluorine ILD Composition								
MAINEFAB CMOS9T 5			5V 200mm 0%											
Reason for Change:														
Continuity of supply.														
Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):														
None														
Changes to product identification resulting from this PCN:														
None														
Product Affected:														
ADS1293CISQ/NOPB LDC1000N			1000L	HRR		LMP	LMP90507CISQX/N			LMP9	9130	0NHZR		
ADS1293CISQE/NOPB LDG			C1000NHRT			LMP	LMP91010DGSR			LMP91300NHZT				
ADS1293CISQX/NOPB LMP9050			05070	7CISQ/NOPB LI			MP91010DGST			LMP91300YZRR				
LDC1000NHRJ LMP905				07CISQE/NOPB LMP9			91300NHZJ			LMP91300YZRT				

Reference Qualification Data: CMOS9T-5V Fluorine Free Process

Reference Quantication Data. Cho591-54 Fluorine Free Process							
Qualification Data: (Approved 4/16/2013)							
This qualification has been developed for the validation of this change. The qualification data will							
validate that the proposed change meets the applicable released technical specifications.							
Qualification Device: LM3533TME (MSL LEVEL1-260C)							
Package Construction Details							
Wafer Fab Site:	MAINE	FAB	Wafer Fab Process:	CMOS9T 5V			
Wafer Diameter:	200mn	n	Metallization:	AI .5%Cu			
Passivation:	OXIDE	/NITRIDE					
Qualification: Plan Test Results							
Deliability Test		Conditions		Sample Size / Fail			
Reliability Test				Lot#1	Lot#2		
High Temp Operating Life		125C (1000 Hrs	77/0	_			
Temp Cycle		-65/150C (500	77/0	77/0			
**Preconditioning: MSL1@260C							
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Qualification Data: (Approved 4/23/2013)							
This qualification has been developed for the validation of this change. The qualification data will							
validate that the proposed change meets the applicable released technical specifications.							
Qualification Device: LM8330TME/NOPB (MSL LEVEL1-260C)							
Package Construction Details							
Wafer Fab Site:	MAINE	FAB	Wafer Fab Process:	CMOS9T 5V			
Wafer Diameter:	200mn	n	Metallization:	AI .5%Cu			
Passivation:	OXIDE,	/NITRIDE					
Qualification: Plan Test Results							
Deliability Test		Canditions		Sample S	Sample Size / Fail		
Reliability Test		Conditions		Lot#1	Lot#2		
High Temp Operating Life		150C (500 Hrs)		77/0	-		
**Preconditioning: MSL1@260C							

For questions regarding this notice, e-mails can be sent to the regional contacts shown below or your local Field Sales Representative.

Location	E-Mail
USA	PCNAmericasContact@list.ti.com
Europe	PCNEuropeContact@list.ti.com
Asia Pacific	PCNAsiaContact@list.ti.com
Japan	PCNJapanContact@list.ti.com